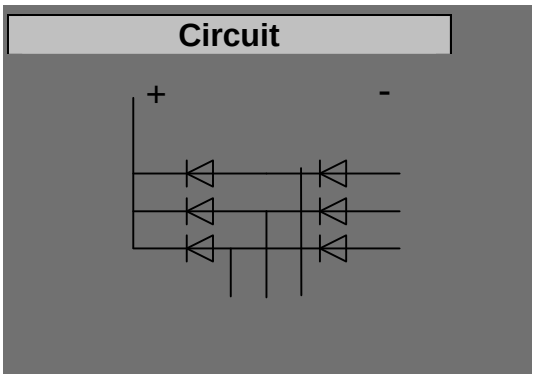

Module Type

Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_D	Output Current(D.C.)	Tc=96 Three phase full wave	200	A
I_{FSM}	Surge forward current	t=10ms,sine, Tvj =45	1900	A
i^2t	Circuit Fusing Consideration	t=10ms,sine, Tvj =45	18050	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
Tvj	Operating Junction Temperature		-40 to +150	
Tstg	Storage Temperature		-40 to +125	
Mt	Mounting Torque	To t erminals(M4)	2±15%	Nm
Mt		To terminals(M6)	5 ± 15%	Nm
Ms		To heatsink(M6)	5 ± 15%	Nm
Weight		Module Approximately	320	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case(TOTAL)	0.12	/W
Rth(c-s)	Thermal Impedance, max.	Case to Heat sink	0.06	/W

Electrical Characteristics

Thyristor
Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_{TAV}	Average On-State Current	Tc=93 , Single Phase half wave 180° conduction	200	A
I_{TSM}	Surge On-State Current			

Electrical and Thermal Characteristics

Performance Curves

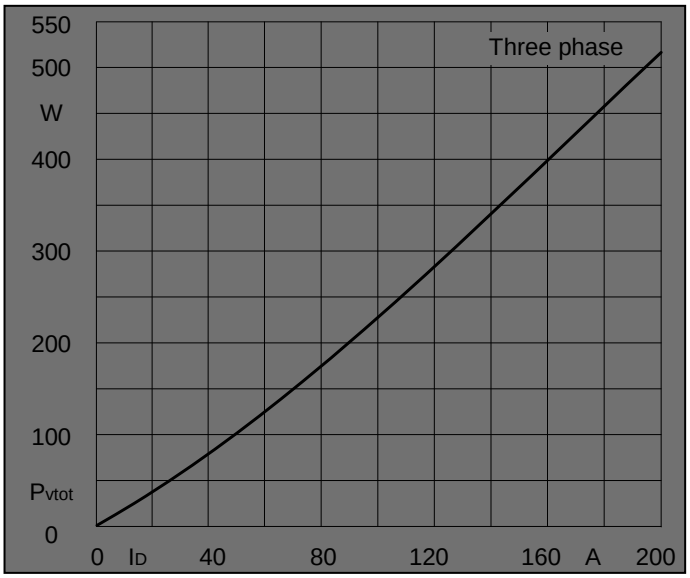

Fig1. Power dissipation

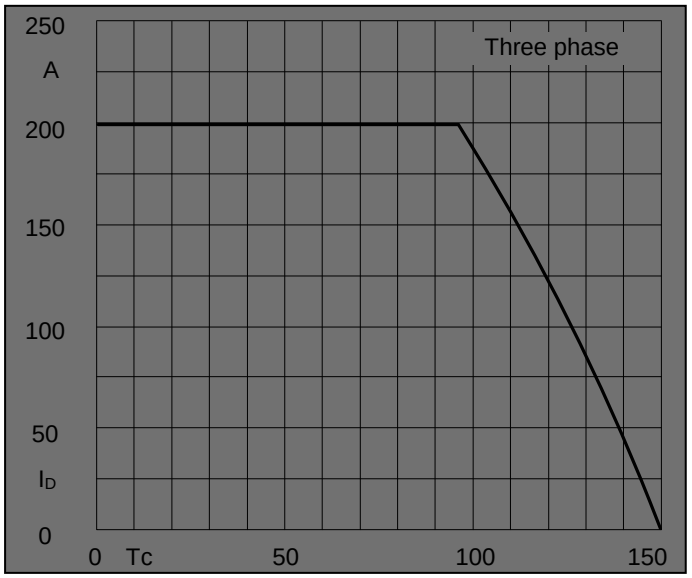

Fig2. Forward Current Derating Curve

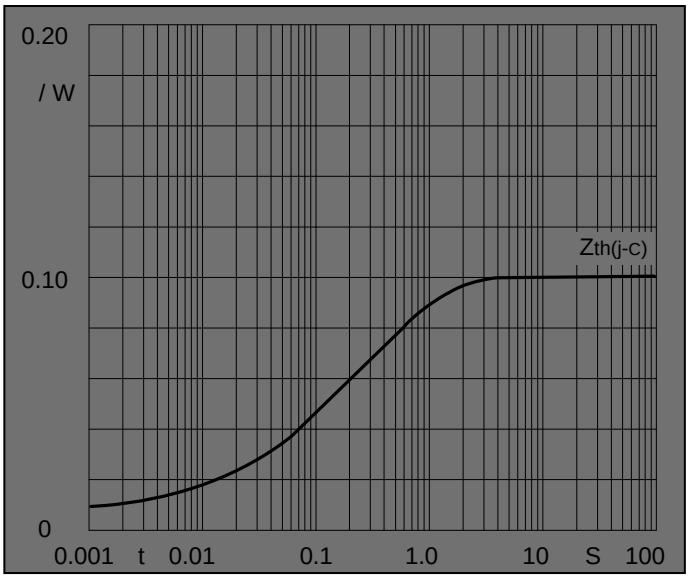

Fig3. Transient thermal impedance

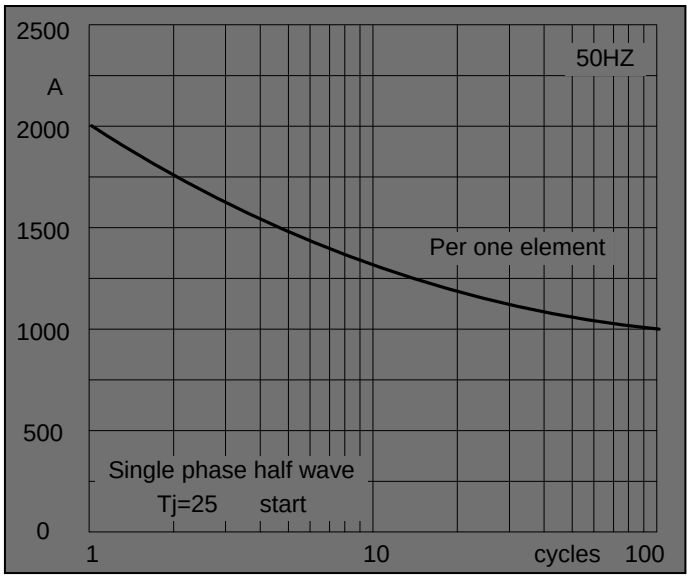

Fig4. Max Non-Repetitive Forward Surge Current

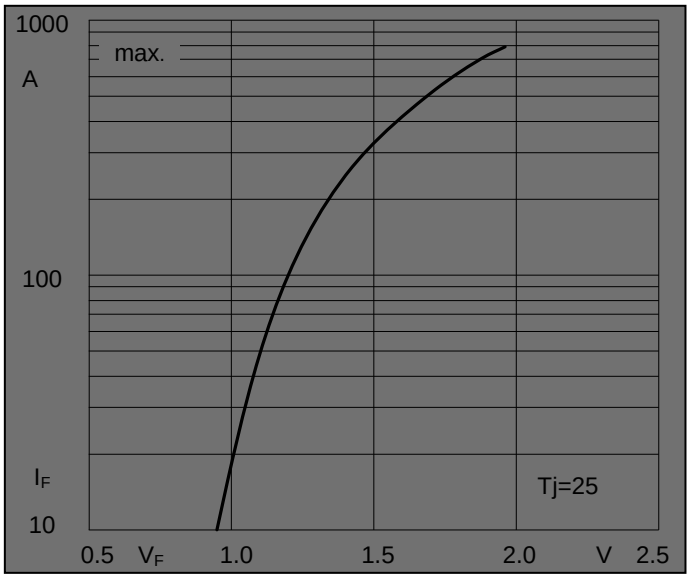

Fig5. Forward Characteristics

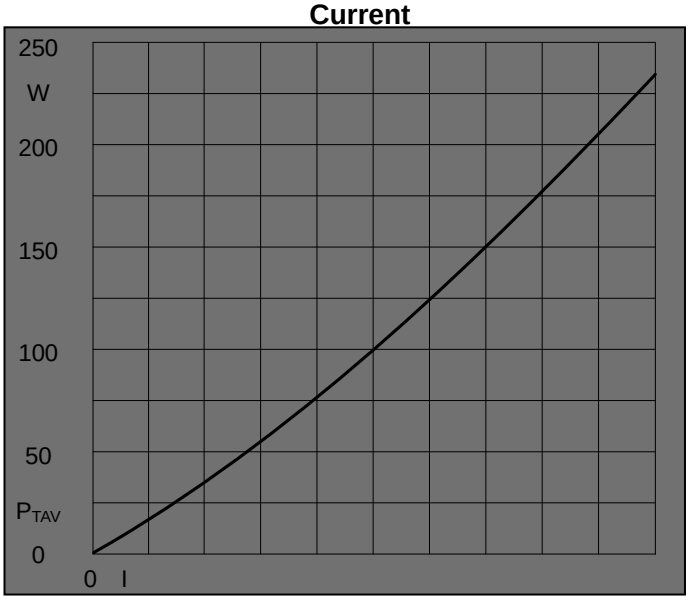

Fig6. SCR Power dissipation

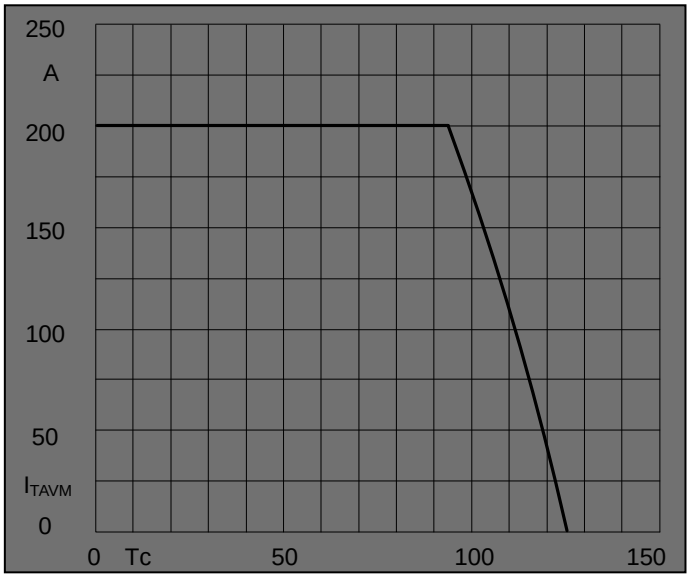

Fig7. SCR Forward Current Derating Curve

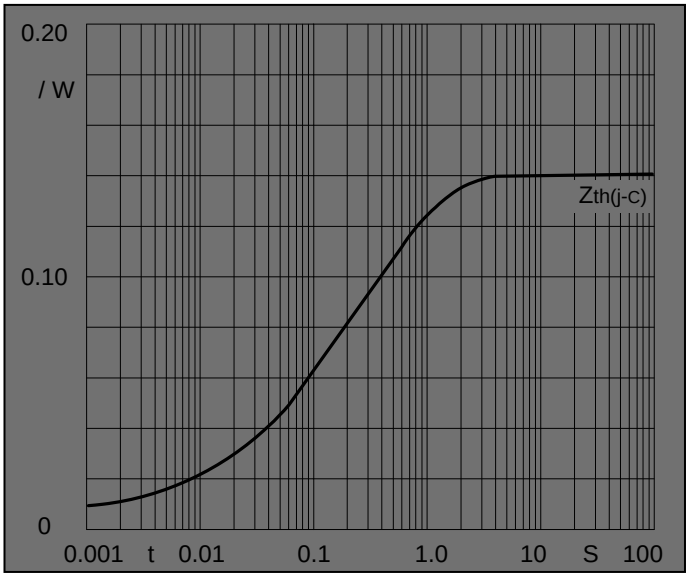

Fig8. SCR Transient thermal impedance

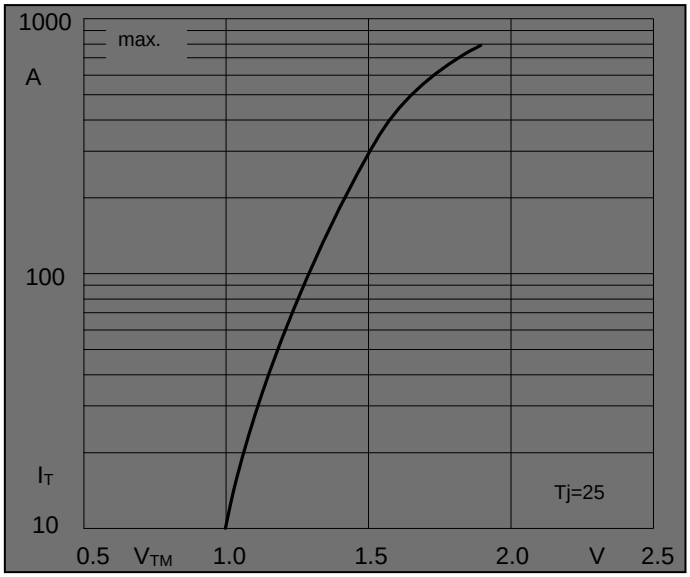

Fig9. SCR Forward Characteristics

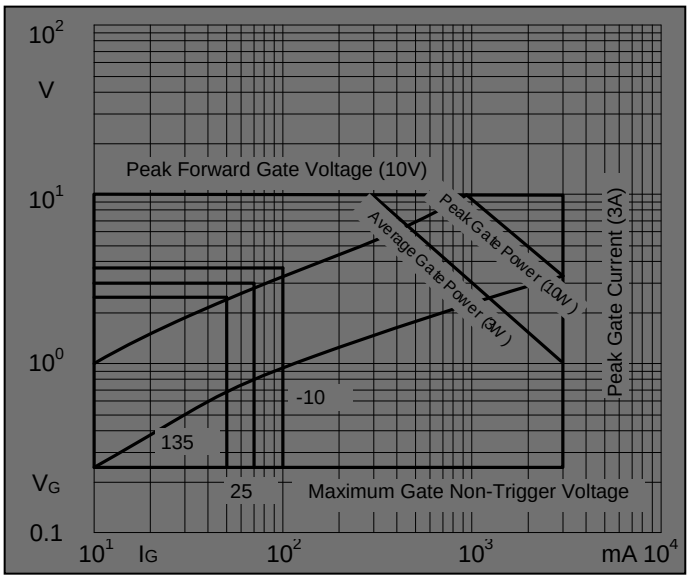

Fig10. Gate trigger Characteristics